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Ferechteh H. Teherani
David C. Look
David J. Rogers
Editors

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Introduction

This volume contains the proceedings of the fifth annual "Oxide Based Materials and Devices" conference which was held at SPIE Photonics West in San Francisco. The conference had its most successful year to date in 2014, with 75 oral and 20 poster presentations of excellent quality from groups in 23 countries covering an ever-widening range of both materials and applications. The conference also attracted a growing industrial interest, with presentations from 20 companies ranging in size from start-ups to multinationals.

The chairs wish to thank the SPIE team for their exemplary organization plus all those who contributed and made this a very lively and stimulating conference. We would also especially like to recognize the efforts of those who took the time to contribute a paper and create this valuable and searchable record of the meeting.

We are looking forward to seeing you in San Francisco next February for "Oxide Based Materials and Devices VI"!

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